

In re application of: Eugene P. Marsh

Serial No.: 10/634,362

Filed: August 8, 2003

For: ATOMIC LAYER DEPOSITION OF METAL DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

§ Group Art Unit: 2812

Examiner: Lynne Ann Gurley

Atty. Docket: 2003-0659.00/US

Confirmation No. 4954

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Certificate of Mailing (37 CFR §1.8)

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to:

Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450, on the date below:

May 20, 2004 Date

INFORMATION DISCLOSURE STATEMENT

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In compliance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant respectfully requests that this Information Disclosure Statement be entered and that the references listed on the attached Form PTO-1449 be considered by the Examiner and made of record. A copy of the listed reference is enclosed.

In accordance with 37 C.F.R. § 1.97(g), this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possible material information as defined in 37 C.F.R. § 1.56(a) exists.

The following reference is submitted for the Examiner's review:

"Cobalt Metallorganic Chemical Vapor Deposition and Formation of Epitaxial CoSi₂ on Si(100) Substrate," Hwa Sung Rhee et al., Journal of the Electrochemical Society, 1999, pp. 2720-2724.

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Serial No.: 10/634,362

Inventor: Eugene P. Marsh

This Information Disclosure Statement is being submitted after the mailing of the first Office Action, but before the mailing of a Final Rejection or Notice of Allowance. The Commissioner is authorized to charge the fee set forth in 37 C.F.R § 1.17(p) of \$180 and any additional fees which may be required to Micron Technology Inc. Deposit Account No.13-3092, Order No. 2003-0659.00/US.

If there are any matters which may be resolved or clarified through telephone interview, the Examiner is respectfully requested to contact Applicant's undersigned agent at the number indicated.

* * * *

Form PTO-1449 is enclosed herewith.

Respectfully submitted,

Kevin D. Martin

Reg. No. 37,882

Micron Technology, Inc. 8000 S. Federal Way

Boise, ID 83706-9632

(208) 368-4516

Agent for Applicant

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EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.